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Titolo	Charge-Trapping Non-Volatile Memories : Volume 2--Emerging Materials and Structures // edited by Panagiotis Dimitrakis
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Nota di contenuto	Materials and Device Reliability in SONOS Memories -- Charge-Trap-Non-Volatile Memory and Focus on Flexible Flash Memory Devices -- Hybrid Memories Based on Redox Molecules -- Organic Floating-Gate Memory Structures -- Nanoparticles Based Flash-like Non Volatile Memories: Cluster Beam Synthesis of Metallic Nanoparticles and Challenges for the Overlying Control Oxide Layer.
Sommario/riassunto	This book describes the technology of charge-trapping non-volatile memories and their uses. The authors explain the device physics of each device architecture and provide a concrete description of the materials involved and the fundamental properties of the technology. Modern material properties, used as charge-trapping layers, for new applications are introduced. Provides a comprehensive overview of the technology for charge-trapping non-volatile memories; Details new

architectures and current modeling concepts for non-volatile memory devices; Focuses on conduction through multi-layer gate dielectrics stacks.
